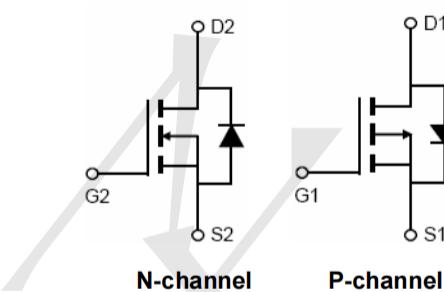


**General Features**

- N-Channel
- $V_{DS} = 30V$ ,  $I_D = 8.0 A$
- $R_{DS(ON)} = 17m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} = 24m\Omega @ V_{GS}=4.5V$
- P-Channel
- $V_{DS} = -30V$ ,  $I_D = -6A$
- $R_{DS(ON)} = 40m\Omega @ V_{GS}=-10V$
- $R_{DS(ON)} = 60m\Omega @ V_{GS}=-4.5V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

**Application**

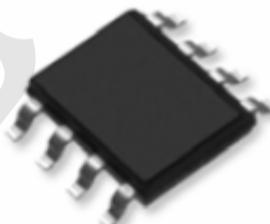
- PWM applications
- DC motor



**Schematic diagram**

S2	1 •	8	D2
G2	2	7	D2
S1	3	6	D1
G1	4	5	D1

**pin assignment**



**SOP-8 top view**

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	$V_{DS}$	30	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V
Continuous Drain Current	$I_D$	8	-6	A
Pulsed Drain Current (Note 1)	$I_{DM}$	25	-20	A
Maximum Power Dissipation	$P_D$	2.5	2.5	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	-55 To 150	°C

### Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note2)	$R_{\theta JA}$	N-Ch	89	°C/W
		P-Ch	90	

### N-CH Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	33	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=24V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.6	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=6A$	-	17	21	$m\Omega$
		$V_{GS}=4.5V, I_D=4A$	-	24	31	$m\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=5A$	-	15	-	S
<b>Dynamic Characteristics (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V, F=1.0MHz$	-	480	-	PF
Output Capacitance	$C_{oss}$		-	80	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	60	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, R_L=3\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	4.5	-	nS
Turn-on Rise Time	$t_r$		-	2.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	14.5	-	nS
Turn-Off Fall Time	$t_f$		-	3.5	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=15V, I_D=5A, V_{GS}=10V$	-	5.2	-	nC
Gate-Source Charge	$Q_{gs}$		-	0.85	-	nC
Gate-Drain Charge	$Q_{gd}$		-	1.3	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=3A$	-	-	1.3	V
Diode Forward Current (Note 2)	$I_S$		-	-	4	A

### N- Channel Typical Electrical and Thermal Characteristics (Curves)

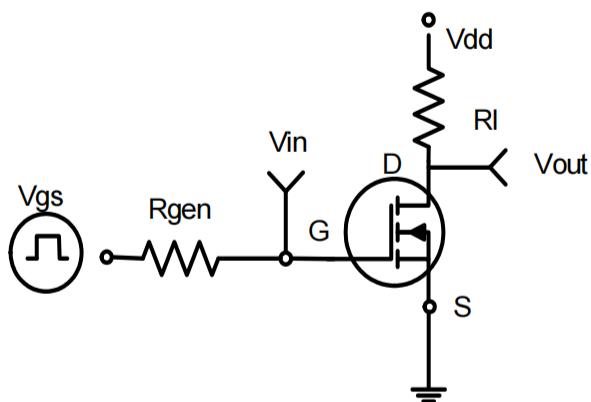


Figure 1:Switching Test Circuit

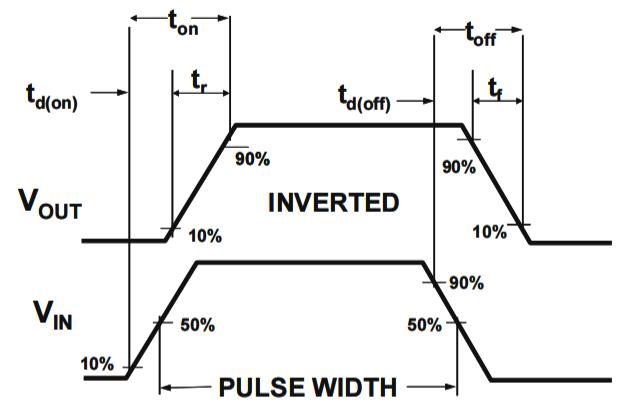


Figure 2:Switching Waveforms

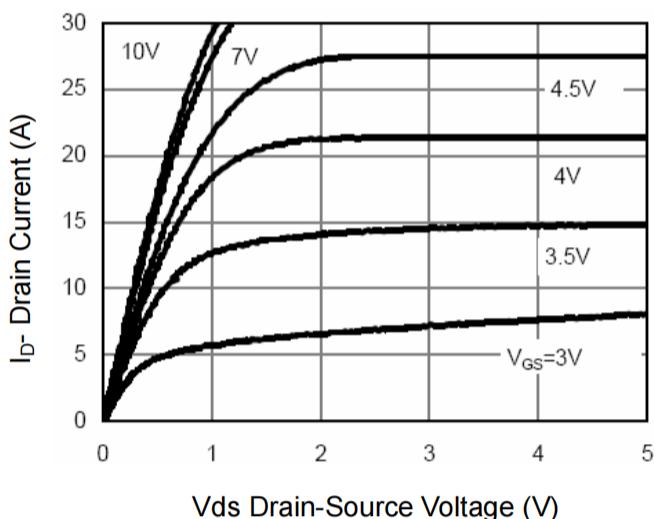
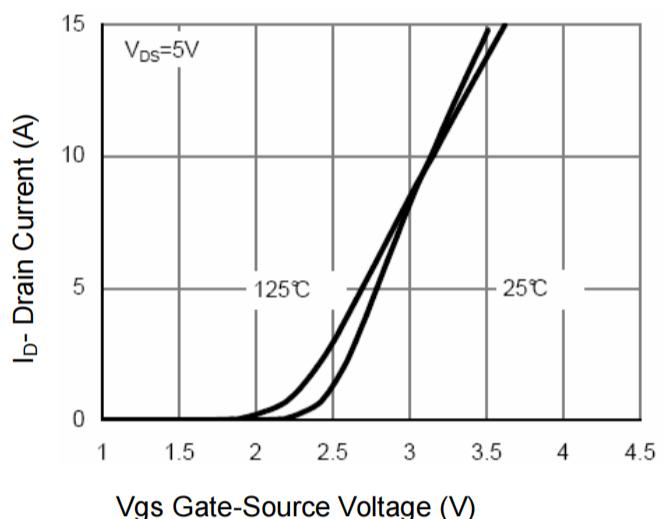
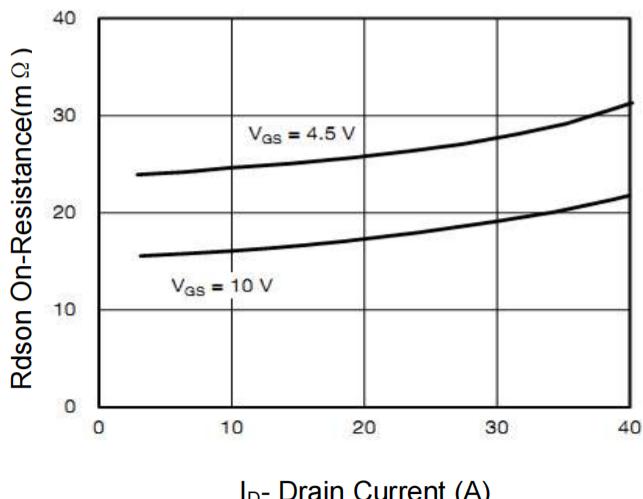


Figure 3 Output Characteristics



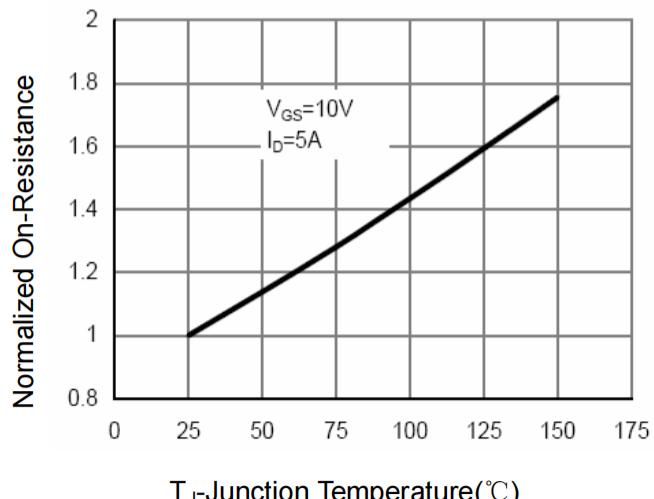
V<sub>DS</sub>=5V

Figure 4 Transfer Characteristics



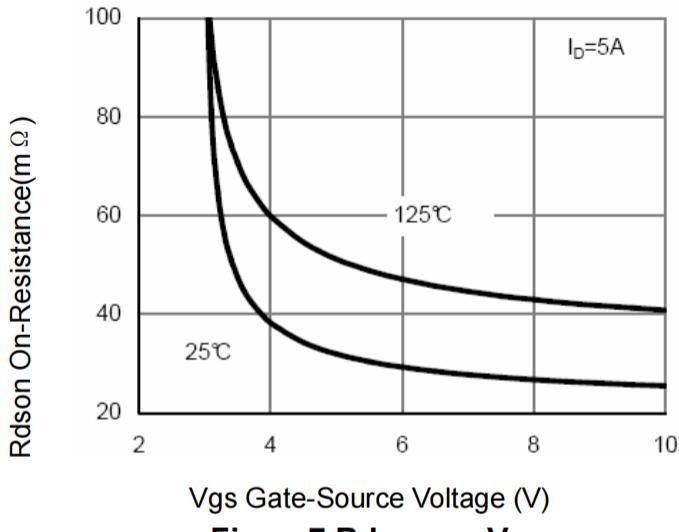
I<sub>D</sub>- Drain Current (A)

Figure 5 Drain-Source On-Resistance

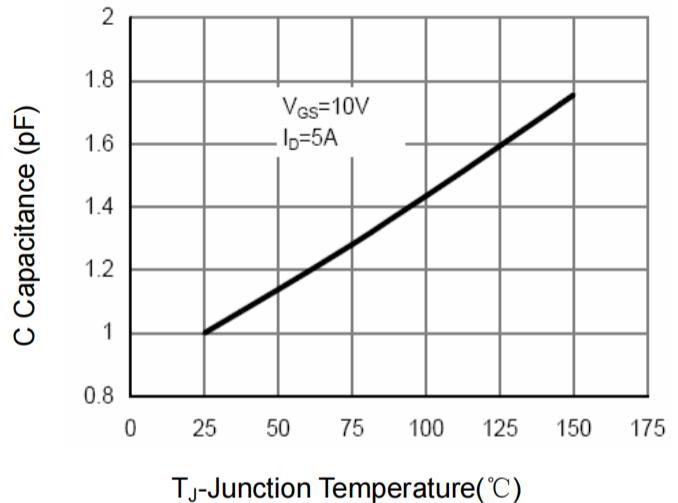


T<sub>J</sub>-Junction Temperature(°C)

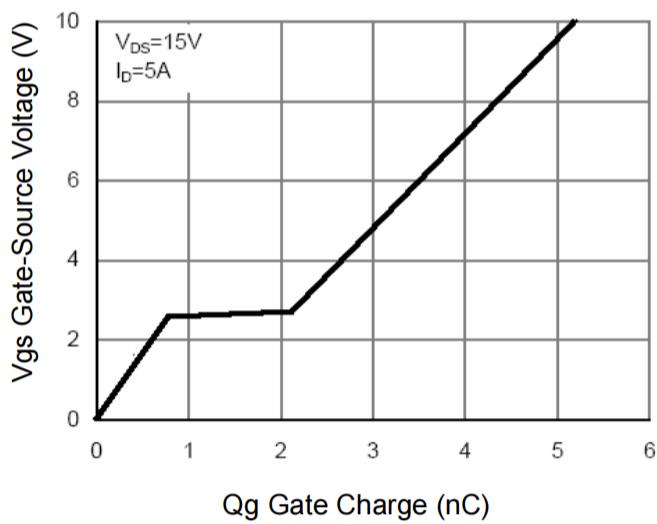
Figure 6 Drain-Source On-Resistance



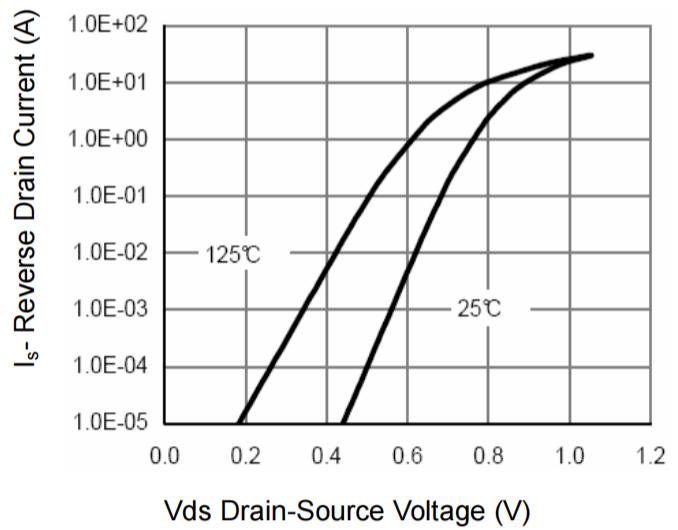
**Figure 7**  $R_{DS(on)}$  vs  $V_{GS}$



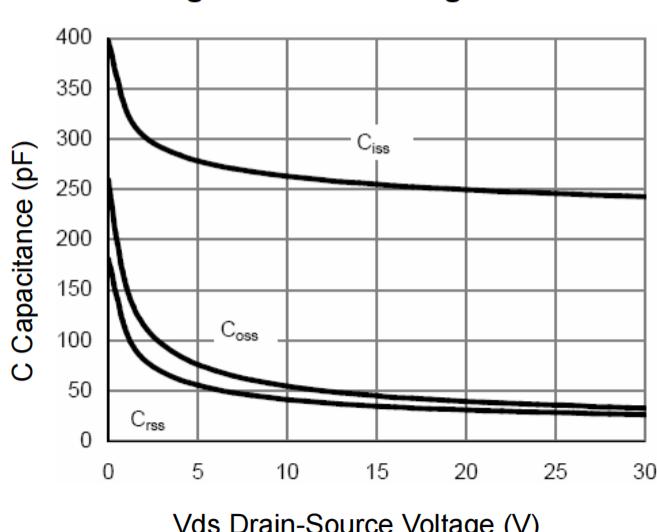
**Figure 8**  $R_{DS(on)}$  vs  $T_J$



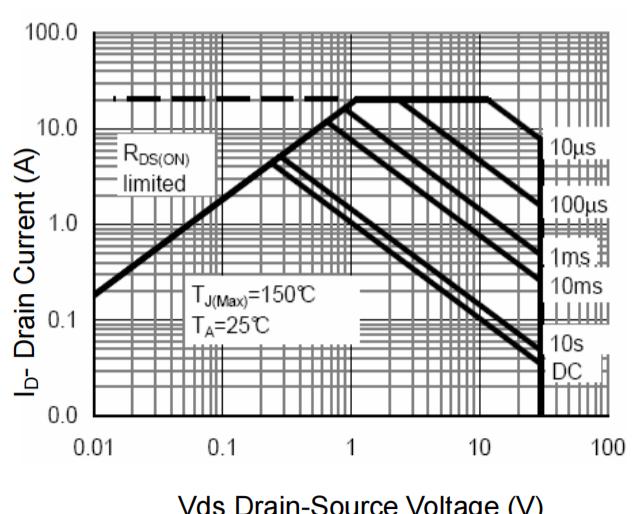
**Figure 9**  $Q_g$  vs  $V_{GS}$



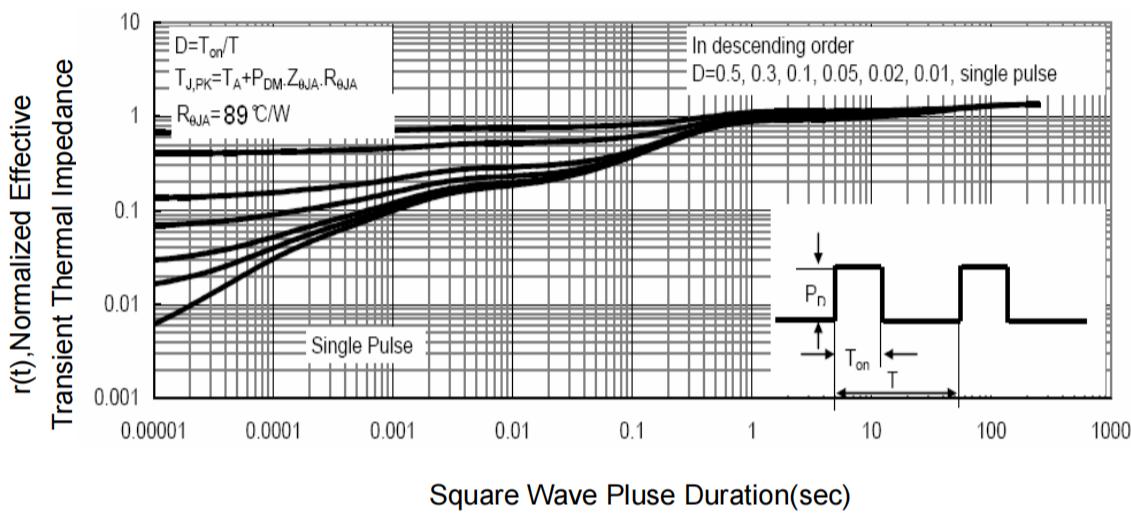
**Figure 10**  $I_S$  vs  $V_{DS}$



**Figure 11**  $C$  vs  $V_{DS}$



**Figure 12** Safe Operation Area



**Figure 13 Normalized Maximum Transient Thermal Impedance**

**P-CH Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30	-33	-	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=-24\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1	-1.5	-2	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-5\text{A}$	-	40	50	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-4\text{A}$	-	60	75	$\text{m}\Omega$
Forward Transconductance	$g_{\text{FS}}$	$V_{\text{DS}}=-5\text{V}, I_{\text{D}}=-4.1\text{A}$	5.5	-	-	S
<b>Dynamic Characteristics (Note 4)</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	648	-	PF
Output Capacitance	$C_{\text{oss}}$		-	108	-	PF
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	68	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=-15\text{V}, R_{\text{L}}=3.6\Omega$ $V_{\text{GS}}=-10\text{V}, R_{\text{GEN}}=3\Omega$	-	9	-	nS
Turn-on Rise Time	$t_r$		-	5	-	nS
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	28	-	nS
Turn-Off Fall Time	$t_f$		-	13.5	-	nS
Total Gate Charge	$Q_g$	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-4\text{A}, V_{\text{GS}}=-10\text{V}$	-	14	-	nC
Gate-Source Charge	$Q_{gs}$		-	3.1	-	nC
Gate-Drain Charge	$Q_{gd}$		-	3.	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_{\text{s}}=-1\text{A}$	-	-	-1.3	V

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production



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**DMC3025LSD**

N&P-Channel Complementary MOSFET

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### P-Channel Typical Electrical and Thermal Characteristics

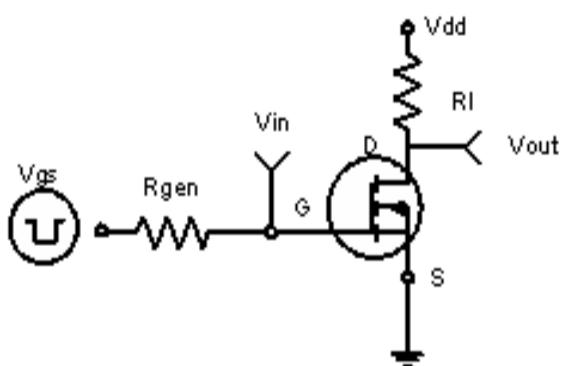


Figure 1:Switching Test Circuit

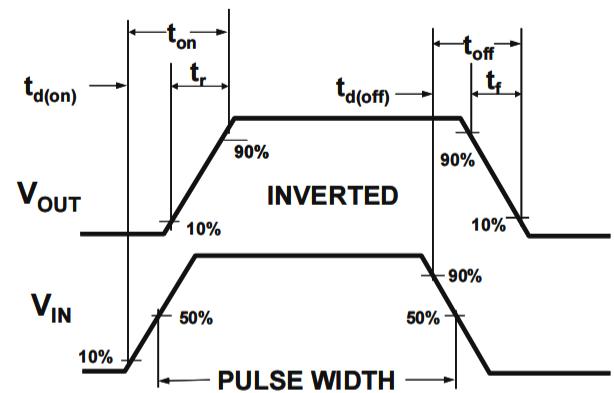
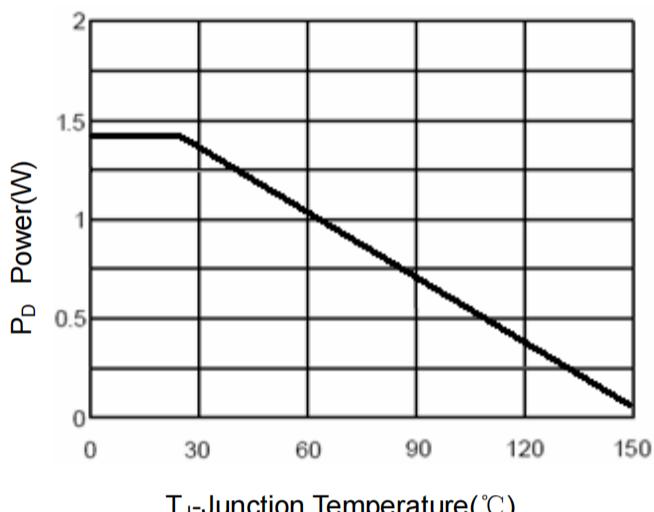
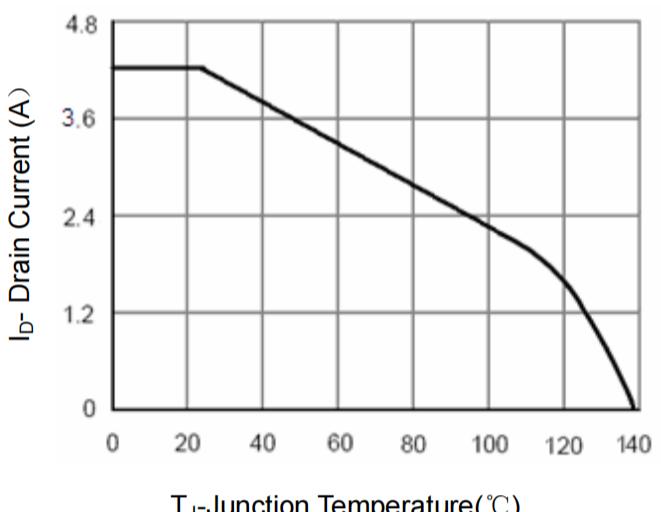


Figure 2:Switching Waveforms



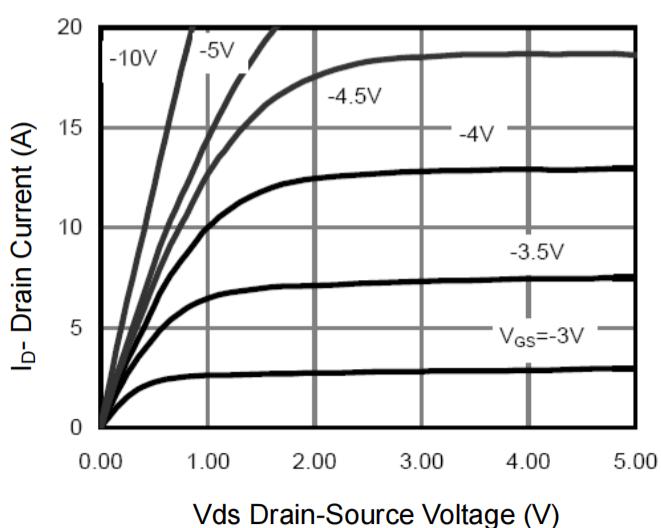
T<sub>j</sub>-Junction Temperature(°C)

Figure 3 Power Dissipation



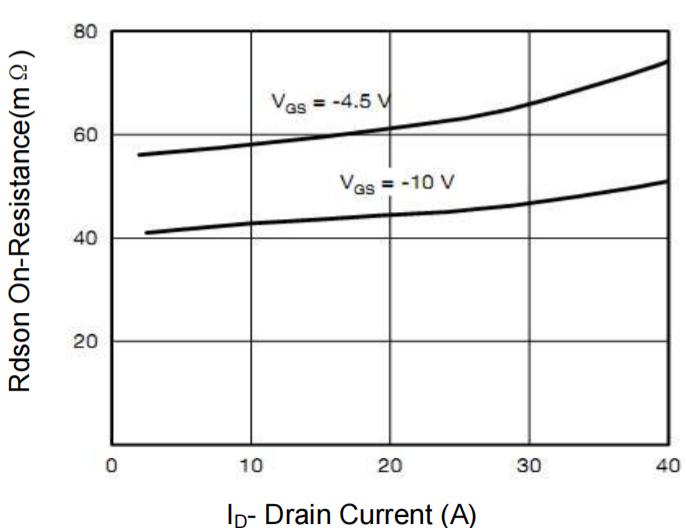
T<sub>j</sub>-Junction Temperature(°C)

Figure 4 Drain Current



V<sub>DS</sub> Drain-Source Voltage (V)

Figure 5 Output CHARACTERISTICS



I<sub>D</sub>- Drain Current (A)

Figure 6 Drain-Source On-Resistance

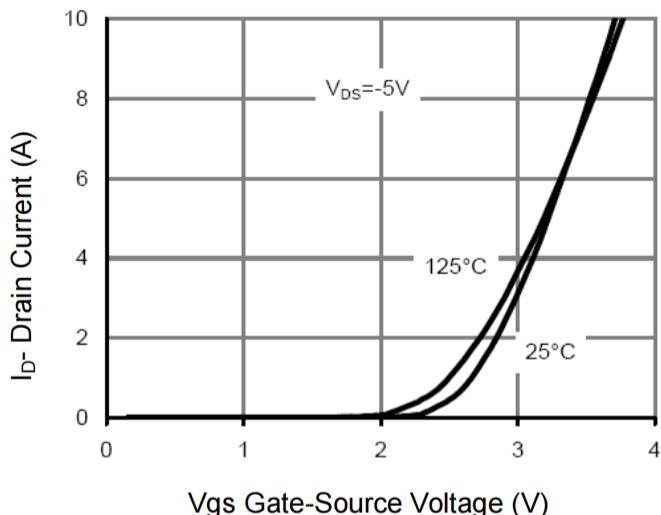


Figure 7 Transfer Characteristics

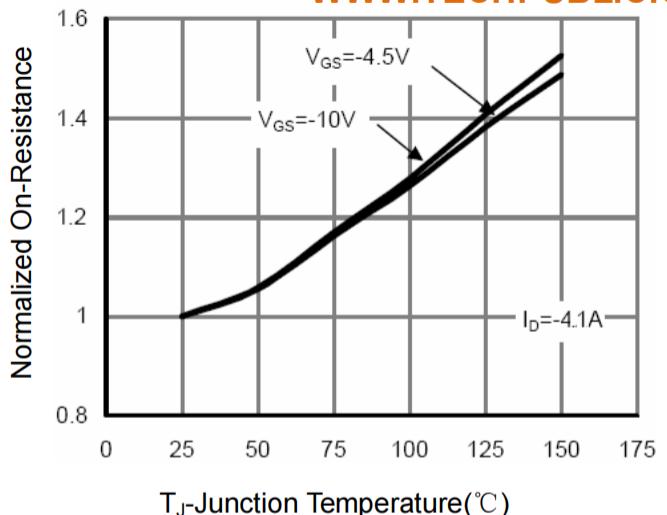


Figure 8 Drain-Source On-Resistance

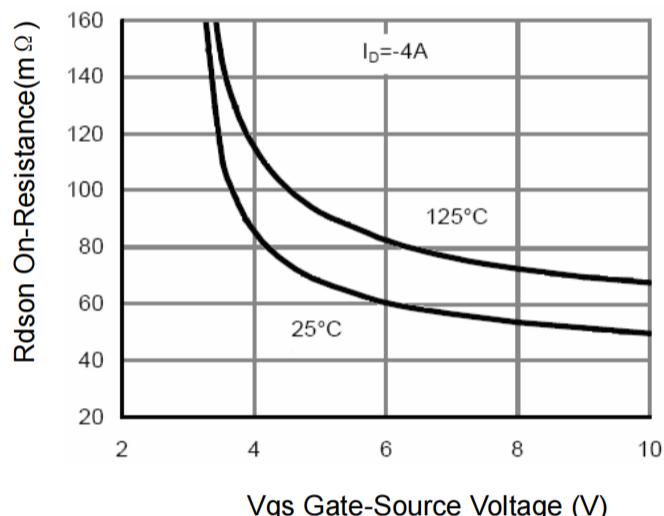


Figure 9  $R_{DS(on)}$  vs  $V_{GS}$

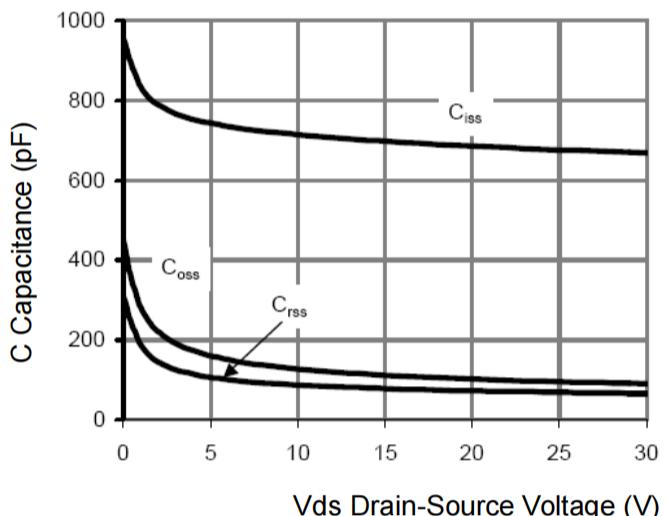


Figure 10 Capacitance vs  $V_{DS}$

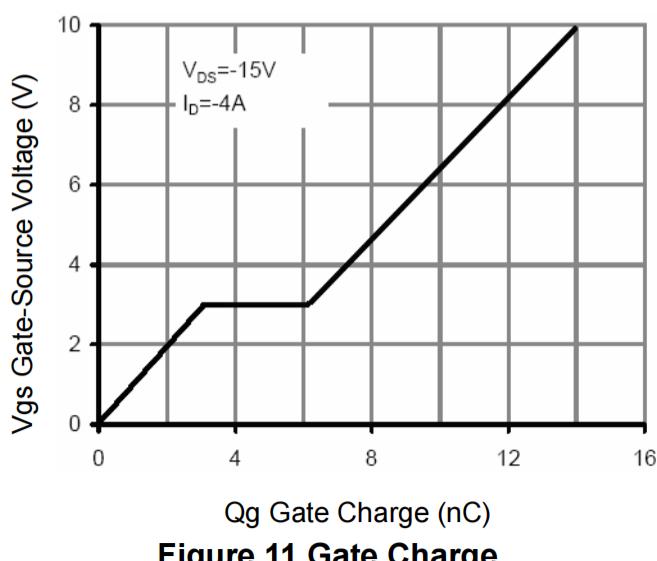


Figure 11 Gate Charge

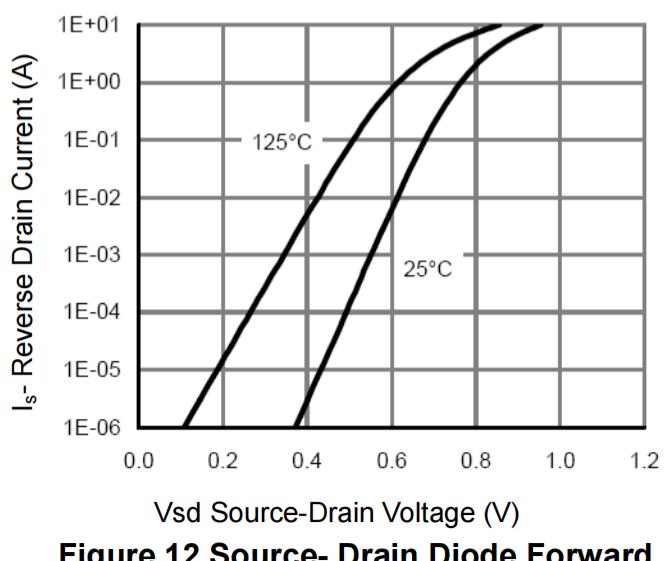
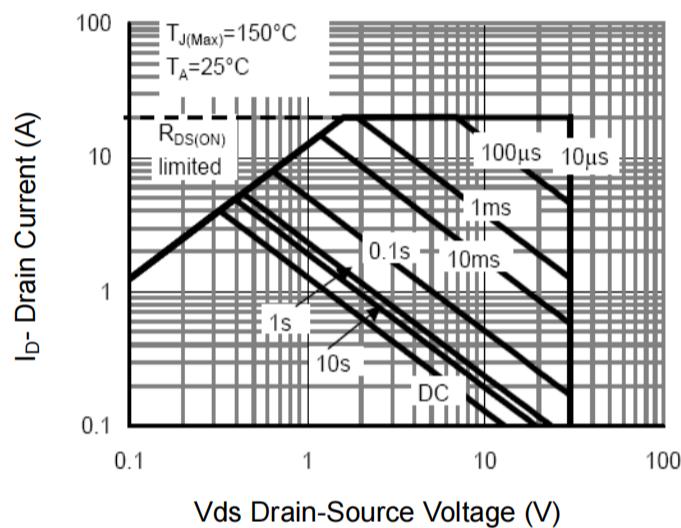
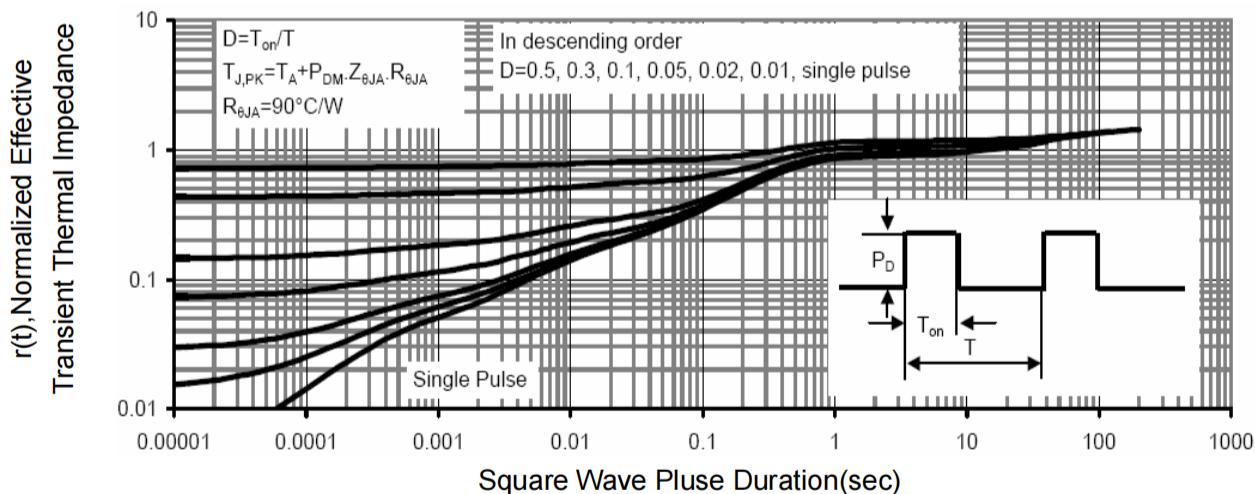


Figure 12 Source-Drain Diode Forward

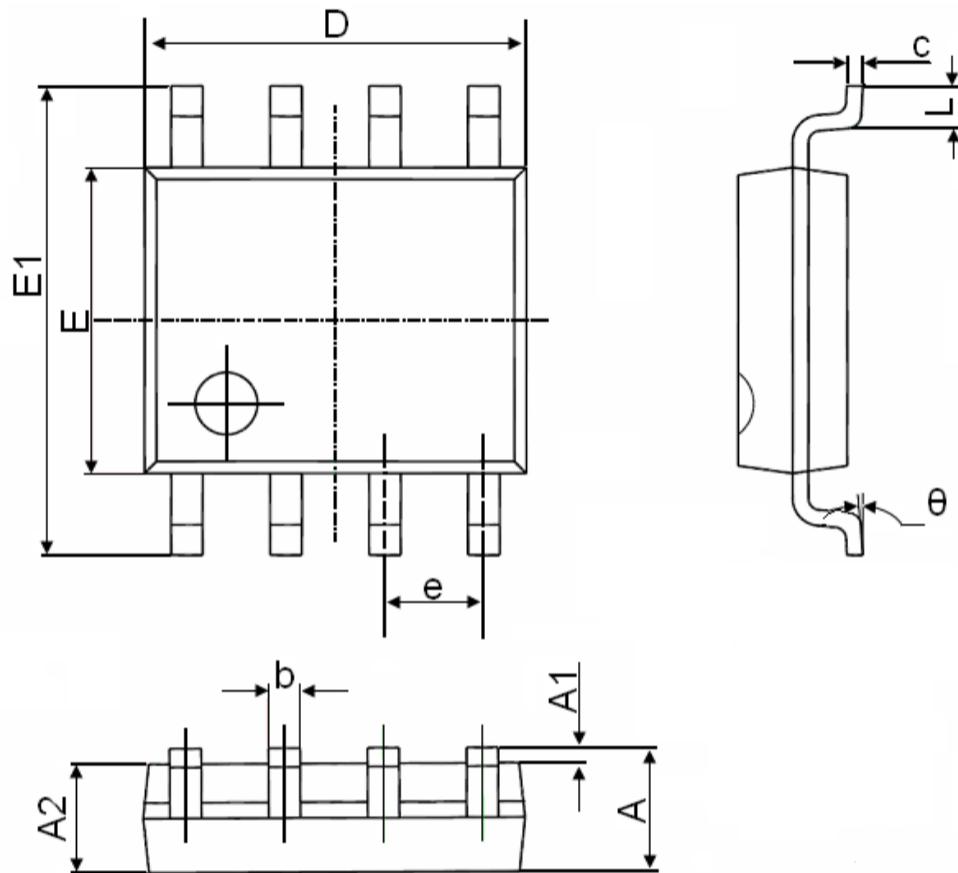


**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

**SOP-8 Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°